

Ming Liu

List of Publications by Citations

Source: <https://exaly.com/author-pdf/10562763/ming-liu-publications-by-citations.pdf>

Version: 2024-04-20

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

215
papers

11,459
citations

57
h-index

99
g-index

228
ext. papers

13,523
ext. citations

6.7
avg, IF

6.32
L-index

#	Paper	IF	Citations
215	Fully room-temperature-fabricated nonvolatile resistive memory for ultrafast and high-density memory application. <i>Nano Letters</i> , 2009 , 9, 1636-43	11.5	718
214	Real-time observation on dynamic growth/dissolution of conductive filaments in oxide-electrolyte-based ReRAM. <i>Advanced Materials</i> , 2012 , 24, 1844-9	24	443
213	Tumor immune microenvironment characterization in clear cell renal cell carcinoma identifies prognostic and immunotherapeutically relevant messenger RNA signatures. <i>Genome Biology</i> , 2016 , 17, 231	18.3	391
212	Controllable growth of nanoscale conductive filaments in solid-electrolyte-based ReRAM by using a metal nanocrystal covered bottom electrode. <i>ACS Nano</i> , 2010 , 4, 6162-8	16.7	371
211	Recommended Methods to Study Resistive Switching Devices. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800143	6.4	297
210	Recent advances in synthesis and surface modification of lanthanide-doped upconversion nanoparticles for biomedical applications. <i>Biotechnology Advances</i> , 2012 , 30, 1551-61	17.8	260
209	Nonpolar Nonvolatile Resistive Switching in Cu Doped ZrO_2 . <i>IEEE Electron Device Letters</i> , 2008 , 29, 434-437	4.4	231
208	Investigation of resistive switching in Cu-doped HfO ₂ thin film for multilevel non-volatile memory applications. <i>Nanotechnology</i> , 2010 , 21, 045202	3.4	228
207	Direct Observation of Conversion Between Threshold Switching and Memory Switching Induced by Conductive Filament Morphology. <i>Advanced Functional Materials</i> , 2014 , 24, 5679-5686	15.6	218
206	Resistive switching memory effect of ZrO ₂ films with Zr ⁺ implanted. <i>Applied Physics Letters</i> , 2008 , 92, 012117	3.4	209
205	Two-dimensional materials for next-generation computing technologies. <i>Nature Nanotechnology</i> , 2020 , 15, 545-557	28.7	196
204	Improvement of Resistive Switching Properties in ZrO_2 -Based ReRAM With Implanted Ti Ions. <i>IEEE Electron Device Letters</i> , 2009 , 30, 1335-1337	4.4	181
203	Nonvolatile resistive switching memory utilizing gold nanocrystals embedded in zirconium oxide. <i>Applied Physics Letters</i> , 2007 , 91, 062111	3.4	172
202	On the resistive switching mechanisms of Cu/ZrO ₂ :Cu/Pt. <i>Applied Physics Letters</i> , 2008 , 93, 223506	3.4	168
201	Eliminating Negative-SET Behavior by Suppressing Nanofilament Overgrowth in Cation-Based Memory. <i>Advanced Materials</i> , 2016 , 28, 10623-10629	24	161
200	Breaking the Current-Retention Dilemma in Cation-Based Resistive Switching Devices Utilizing Graphene with Controlled Defects. <i>Advanced Materials</i> , 2018 , 30, e1705193	24	157
199	Distance-dependent plasmon-enhanced fluorescence of upconversion nanoparticles using polyelectrolyte multilayers as tunable spacers. <i>Scientific Reports</i> , 2015 , 5, 7779	4.9	144

198	Multilevel resistive switching with ionic and metallic filaments. <i>Applied Physics Letters</i> , 2009 , 94, 233106	3.4	142
197	Quantum-size effects in hafnium-oxide resistive switching. <i>Applied Physics Letters</i> , 2013 , 102, 183505	3.4	139
196	Resistive Switching Properties of $\text{Au}/\text{ZrO}_2/\text{Ag}$ Structure for Low-Voltage Nonvolatile Memory Applications. <i>IEEE Electron Device Letters</i> , 2010 , 31, 117-119	4.4	123
195	Voltage and power-controlled regimes in the progressive unipolar RESET transition of HfO ₂ -based RRAM. <i>Scientific Reports</i> , 2013 , 3, 2929	4.9	118
194	Light-Gated Memristor with Integrated Logic and Memory Functions. <i>ACS Nano</i> , 2017 , 11, 11298-11305	16.7	116
193	Confining Cation Injection to Enhance CBRAM Performance by Nanopore Graphene Layer. <i>Small</i> , 2017 , 13, 1603948	11	113
192	A Model for the Set Statistics of RRAM Inspired in the Percolation Model of Oxide Breakdown. <i>IEEE Electron Device Letters</i> , 2013 , 34, 999-1001	4.4	111
191	Resistive Switching Performance Improvement via Modulating Nanoscale Conductive Filament, Involving the Application of Two-Dimensional Layered Materials. <i>Small</i> , 2017 , 13, 1604306	11	105
190	An artificial spiking afferent nerve based on Mott memristors for neurorobotics. <i>Nature Communications</i> , 2020 , 11, 51	17.4	105
189	Evolution of conductive filament and its impact on reliability issues in oxide-electrolyte based resistive random access memory. <i>Scientific Reports</i> , 2015 , 5, 7764	4.9	99
188	Controlling the growth of single crystalline nanoribbons of copper tetracyanoquinodimethane for the fabrication of devices and device arrays. <i>Journal of the American Chemical Society</i> , 2006 , 128, 12917-22	16.4	97
187	Formation of multiple conductive filaments in the Cu/ZrO ₂ :Cu/Pt device. <i>Applied Physics Letters</i> , 2009 , 95, 023501	3.4	95
186	Emulating Short-Term and Long-Term Plasticity of Bio-Synapse Based on Cu/a-Si/Pt Memristor. <i>IEEE Electron Device Letters</i> , 2017 , 38, 1208-1211	4.4	89
185	Atomic-level quantized reaction of HfO _x memristor. <i>Applied Physics Letters</i> , 2013 , 102, 172903	3.4	88
184	Cycle-to-Cycle Intrinsic RESET Statistics in HfO_2 -Based Unipolar RRAM Devices. <i>IEEE Electron Device Letters</i> , 2013 , 34, 623-625	4.4	88
183	Transcriptomic Profiling of the Tumor Microenvironment Reveals Distinct Subgroups of Clear Cell Renal Cell Cancer: Data from a Randomized Phase III Trial. <i>Cancer Discovery</i> , 2019 , 9, 510-525	24.4	88
182	The <i>Drosophila</i> female germline stem cell lineage acts to spatially restrict DPP function within the niche. <i>Science Signaling</i> , 2010 , 3, ra57	8.8	87
181	Analysis and modeling of resistive switching statistics. <i>Journal of Applied Physics</i> , 2012 , 111, 074508	2.5	83

180	Electronic imitation of behavioral and psychological synaptic activities using TiO/AlO-based memristor devices. <i>Nanoscale</i> , 2017 , 9, 14442-14450	7.7	76
179	Cancer immunotherapy via targeted TGF- β signalling blockade in T cells. <i>Nature</i> , 2020 , 587, 121-125	50.4	76
178	Full imitation of synaptic metaplasticity based on memristor devices. <i>Nanoscale</i> , 2018 , 10, 5875-5881	7.7	75
177	Thermoelectric Seebeck effect in oxide-based resistive switching memory. <i>Nature Communications</i> , 2014 , 5, 4598	17.4	75
176	FPGA Based on Integration of CMOS and RRAM. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2011 , 19, 2023-2032	2.6	74
175	Super non-linear RRAM with ultra-low power for 3D vertical nano-crossbar arrays. <i>Nanoscale</i> , 2016 , 8, 15629-36	7.7	72
174	Cancer Cell Membrane-Biomimetic Nanoprobes with Two-Photon Excitation and Near-Infrared Emission for Intravital Tumor Fluorescence Imaging. <i>ACS Nano</i> , 2018 , 12, 1350-1358	16.7	71
173	A review of carrier thermoelectric-transport theory in organic semiconductors. <i>Physical Chemistry Chemical Physics</i> , 2016 , 18, 19503-25	3.6	71
172	Effects of Capping Electrode on Ferroelectric Properties of Hf _{0.5} Zr _{0.5} O ₂ Thin Films. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1207-1210	4.4	70
171	Metal-Semiconductor-Metal (Ga ₂ O ₃) Solar-Blind Photodetectors with a Record-High Responsivity Rejection Ratio and Their Gain Mechanism. <i>ACS Photonics</i> , 2020 , 7, 812-820	6.3	69
170	Self-rectifying effect in gold nanocrystal-embedded zirconium oxide resistive memory. <i>Journal of Applied Physics</i> , 2009 , 106, 073724	2.5	69
169	Recent updates on cancer immunotherapy. <i>Precision Clinical Medicine</i> , 2018 , 1, 65-74	6.7	66
168	Atomic View of Filament Growth in Electrochemical Memristive Elements. <i>Scientific Reports</i> , 2015 , 5, 13311	4.9	65
167	Conductance Quantization in Resistive Random Access Memory. <i>Nanoscale Research Letters</i> , 2015 , 10, 420	5	65
166	Organic nonpolar nonvolatile resistive switching in poly(3,4-ethylene-dioxythiophene): Polystyrenesulfonate thin film. <i>Organic Electronics</i> , 2009 , 10, 1191-1194	3.5	65
165	Enhancement of the Thermoelectric Performance of Polycrystalline In ₄ Se _{2.5} by Copper Intercalation and Bromine Substitution. <i>Advanced Energy Materials</i> , 2014 , 4, 1300599	21.8	64
164	Performance enhancement of multilevel cell nonvolatile memory by using a bandgap engineered high-trapping layer. <i>Applied Physics Letters</i> , 2010 , 97, 253503	3.4	63
163	TGF- β suppresses type 2 immunity to cancer. <i>Nature</i> , 2020 , 587, 115-120	50.4	63

162	Quinoxaline-based conjugated polymers for polymer solar cells. <i>Polymer Chemistry</i> , 2017 , 8, 4613-4636	4.9	62
161	Enhanced DNA Sequencing Performance Through Edge-Hydrogenation of Graphene Electrodes. <i>Advanced Functional Materials</i> , 2011 , 21, 2674-2679	15.6	60
160	Reset Statistics of NiO-Based Resistive Switching Memories. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1570-1572	4.7	60
159	High-Performance Metal-Organic Chemical Vapor Deposition Grown ϵ -Ga ₂ O ₃ Solar-Blind Photodetector With Asymmetric Schottky Electrodes. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1475-1478	4.4	59
158	Fused Perylene Diimide-Based Polymeric Acceptors for Efficient All-Polymer Solar Cells. <i>Macromolecules</i> , 2017 , 50, 7559-7566	5.5	57
157	Resistive random access memory (RRAM) technology: From material, device, selector, 3D integration to bottom-up fabrication. <i>Journal of Electroceramics</i> , 2017 , 39, 21-38	1.5	57
156	Fatigue mechanism of yttrium-doped hafnium oxide ferroelectric thin films fabricated by pulsed laser deposition. <i>Physical Chemistry Chemical Physics</i> , 2017 , 19, 3486-3497	3.6	56
155	Photoelectric Plasticity in Oxide Thin Film Transistors with Tunable Synaptic Functions. <i>Advanced Electronic Materials</i> , 2018 , 4, 1800556	6.4	56
154	An overview of resistive random access memory devices. <i>Science Bulletin</i> , 2011 , 56, 3072-3078		55
153	Synthesis of upconversion NaYF ₄ :Yb ³⁺ ,Er ³⁺ particles with enhanced luminescent intensity through control of morphology and phase. <i>Journal of Materials Chemistry C</i> , 2014 , 2, 3671-3676	7.1	54
152	In situ observation of nickel as an oxidizable electrode material for the solid-electrolyte-based resistive random access memory. <i>Applied Physics Letters</i> , 2013 , 102, 053502	3.4	54
151	Uniformity Improvement in 1T1R RRAM With Gate Voltage Ramp Programming. <i>IEEE Electron Device Letters</i> , 2014 , 35, 1224-1226	4.4	54
150	Novel perylene diimide-based polymers with electron-deficient segments as the comonomer for efficient all-polymer solar cells. <i>Journal of Materials Chemistry A</i> , 2018 , 6, 414-422	13	54
149	Organic thin-film transistor memory with gold nanocrystals embedded in polyimide gate dielectric. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 135111	3	51
148	Amorphous Gallium Oxide-Based Gate-Tunable High-Performance Thin Film Phototransistor for Solar-Blind Imaging. <i>Advanced Electronic Materials</i> , 2019 , 5, 1900389	6.4	50
147	Nitrogen-induced improvement of resistive switching uniformity in a HfO ₂ -based RRAM device. <i>Semiconductor Science and Technology</i> , 2012 , 27, 125008	1.8	50
146	Resistive switching characteristics of MnO _x -based ReRAM. <i>Journal Physics D: Applied Physics</i> , 2009 , 42, 055112	3	50
145	Fabrication and charging characteristics of MOS capacitor structure with metal nanocrystals embedded in gate oxide. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 2754-2758	3	50

144	General Einstein relation model in disordered organic semiconductors under quasiequilibrium. <i>Physical Review B</i> , 2014 , 90,	3-3	49
143	Spiral photon sieves apodized by digital prolate spheroidal window for the generation of hard-x-ray vortex. <i>Optics Letters</i> , 2010 , 35, 1765-7	3	49
142	Highly Stable Radiation-Hardened Resistive-Switching Memory. <i>IEEE Electron Device Letters</i> , 2010 , 31, 1470-1472	4-4	49
141	Oxide-Based Electrolyte-Gated Transistors for Spatiotemporal Information Processing. <i>Advanced Materials</i> , 2020 , 32, e2003018	24	48
140	An experimental study of the interaction between tar and SOFCs with Ni/GDC anodes. <i>Applied Energy</i> , 2013 , 108, 149-157	10.7	47
139	Design of CMOS Compatible, High-Speed, Highly-Stable Complementary Switching with Multilevel Operation in 3D Vertically Stacked Novel HfO ₂ /Al ₂ O ₃ /TiO _x (HAT) RRAM. <i>Advanced Electronic Materials</i> , 2018 , 4, 1700561	6.4	45
138	Multi-scale quantum point contact model for filamentary conduction in resistive random access memories devices. <i>Journal of Applied Physics</i> , 2014 , 115, 244507	2.5	45
137	Bipolar one diode-one resistor integration for high-density resistive memory applications. <i>Nanoscale</i> , 2013 , 5, 4785-9	7-7	45
136	Improvement of durability and switching speed by incorporating nanocrystals in the HfO _x based resistive random access memory devices. <i>Applied Physics Letters</i> , 2018 , 113, 023105	3-4	44
135	Superior Retention of Low-Resistance State in Conductive Bridge Random Access Memory With Single Filament Formation. <i>IEEE Electron Device Letters</i> , 2015 , 36, 129-131	4-4	44
134	Improvement of resistive switching characteristics in ZrO ₂ film by embedding a thin TiO _x layer. <i>Nanotechnology</i> , 2011 , 22, 254028	3-4	43
133	Review of deep ultraviolet photodetector based on gallium oxide. <i>Chinese Physics B</i> , 2019 , 28, 018501	1.2	42
132	Proton-based total-dose irradiation effects on Cu/HfO ₂ :Cu/Pt ReRAM devices. <i>Nanotechnology</i> , 2010 , 21, 475206	3-4	42
131	Improvement of Endurance in HZO-Based Ferroelectric Capacitor Using Ru Electrode. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1744-1747	4-4	41
130	Improved Resistive Switching Uniformity in $\text{Cu}/\text{HfO}_2/\text{Pt}$ Devices by Using Current Sweeping Mode. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1053-1055	4-4	41
129	Enhancement-Mode $\beta\text{-Ga}_2\text{O}_3$ Metal-Oxide-Semiconductor Field-Effect Solar-Blind Phototransistor With Ultrahigh Detectivity and Photo-to-Dark Current Ratio. <i>IEEE Electron Device Letters</i> , 2019 , 40, 742-745	4-4	40
128	Characterization of the inhomogeneous barrier distribution in a Pt/(100)Ga ₂ O ₃ Schottky diode via its temperature-dependent electrical properties. <i>AIP Advances</i> , 2018 , 8, 015316	1.5	39
127	Set statistics in conductive bridge random access memory device with Cu/HfO ₂ /Pt structure. <i>Applied Physics Letters</i> , 2014 , 105, 193501	3-4	39

126	Nonvolatile nano-crystal floating gate OFET memory with light assisted program. <i>Organic Electronics</i> , 2011 , 12, 1236-1240	3.5	39
125	Anode recirculation behavior of a solid oxide fuel cell system: A safety analysis and a performance optimization. <i>International Journal of Hydrogen Energy</i> , 2013 , 38, 2868-2883	6.7	38
124	Conduction mechanism of a TaO(x)-based selector and its application in crossbar memory arrays. <i>Nanoscale</i> , 2015 , 7, 4964-70	7.7	38
123	Performance-Enhancing Selector via Symmetrical Multilayer Design. <i>Advanced Functional Materials</i> , 2019 , 29, 1808376	15.6	38
122	Multiple heteroatom induced carrier engineering and hierarchical nanostructures for high thermoelectric performance of polycrystalline In ₄ Se _{2.5} . <i>Journal of Materials Chemistry A</i> , 2015 , 3, 1251-1257	13.7	37
121	Universal carrier thermoelectric-transport model based on percolation theory in organic semiconductors. <i>Physical Review B</i> , 2015 , 91,	3.3	37
120	Ultrahigh-Performance Solar-Blind Photodetector Based on α -Phase- Dominated Ga ₂ O ₃ Film With Record Low Dark Current of 81 fA. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1483-1486	4.4	36
119	Occurrence of Resistive Switching and Threshold Switching in Atomic Layer Deposited Ultrathin (2 nm) Aluminium Oxide Crossbar Resistive Random Access Memory. <i>IEEE Electron Device Letters</i> , 2015 , 36, 333-335	4.4	36
118	Resistance switching of Au-implanted-ZrO ₂ film for nonvolatile memory application. <i>Journal of Applied Physics</i> , 2008 , 104, 114514	2.5	36
117	Physical model of dynamic Joule heating effect for reset process in conductive-bridge random access memory. <i>Journal of Computational Electronics</i> , 2014 , 13, 432-438	1.8	35
116	Square optical vortices generated by binary spiral zone plates. <i>Applied Physics Letters</i> , 2011 , 98, 151106	3.4	35
115	Variability Improvement of TiO ₂ /AlO _x Bilayer Nonvolatile Resistive Switching Devices by Interfacial Band Engineering with an Ultrathin AlO Dielectric Material. <i>ACS Omega</i> , 2017 , 2, 6888-6895	3.9	34
114	Multilevel unipolar resistive switching with negative differential resistance effect in Ag/SiO ₂ /Pt device. <i>Journal of Applied Physics</i> , 2014 , 116, 154509	2.5	34
113	TGF-Control of Adaptive Immune Tolerance: A Break From Treg Cells. <i>BioEssays</i> , 2018 , 40, e1800063	4.1	33
112	Recent Development on Narrow Bandgap Conjugated Polymers for Polymer Solar Cells. <i>Polymers</i> , 2017 , 9,	4.5	32
111	Investigation of resistive switching behaviours in WO ₃ -based RRAM devices. <i>Chinese Physics B</i> , 2011 , 20, 017305	1.2	32
110	Nonvolatile multilevel memory effect in Cu/WO ₃ /Pt device structures. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 124-126	2.5	32
109	Bipolar Analog Memristors as Artificial Synapses for Neuromorphic Computing. <i>Materials</i> , 2018 , 11,	3.5	32

108	Crystal that remembers: several ways to utilize nanocrystals in resistive switching memory. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 303002	3	31
107	Improving resistance uniformity and endurance of resistive switching memory by accurately controlling the stress time of pulse program operation. <i>Applied Physics Letters</i> , 2015 , 106, 092103	3.4	30
106	Charge carrier hopping transport based on Marcus theory and variable-range hopping theory in organic semiconductors. <i>Journal of Applied Physics</i> , 2015 , 118, 045701	2.5	30
105	Intrinsic anionic rearrangement by extrinsic control: transition of RS and CRS in thermally elevated TiN/HfO/Pt RRAM. <i>Nanoscale</i> , 2017 , 9, 18908-18917	7.7	30
104	Modeling of retention characteristics for metal and semiconductor nanocrystal memories. <i>Solid-State Electronics</i> , 2007 , 51, 806-811	1.7	29
103	Complementary Switching in 3D Resistive Memory Array. <i>Advanced Electronic Materials</i> , 2017 , 3, 1700287	4	28
102	Single-cell sequencing links multiregional immune landscapes and tissue-resident T cells in ccRCC to tumor topology and therapy efficacy. <i>Cancer Cell</i> , 2021 , 39, 662-677.e6	24.3	28
101	Impact of program/erase operation on the performances of oxide-based resistive switching memory. <i>Nanoscale Research Letters</i> , 2015 , 10, 39	5	27
100	Dynamic observation of oxygen vacancies in hafnia layer by in situ transmission electron microscopy. <i>Nano Research</i> , 2015 , 8, 3571-3579	10	27
99	Foxp3-independent mechanism by which TGF- β controls peripheral T cell tolerance. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2017 , 114, E7536-E7544	11.5	27
98	YAP regulates the expression of Hoxa1 and Hoxc13 in mouse and human oral and skin epithelial tissues. <i>Molecular and Cellular Biology</i> , 2015 , 35, 1449-61	4.8	27
97	A review for polaron dependent charge transport in organic semiconductor. <i>Organic Electronics</i> , 2018 , 61, 223-234	3.5	26
96	The fate of tars under solid oxide fuel cell conditions: A review. <i>Applied Thermal Engineering</i> , 2014 , 70, 687-693	5.8	26
95	Overcoming the Dilemma Between RESET Current and Data Retention of RRAM by Lateral Dissolution of Conducting Filament. <i>IEEE Electron Device Letters</i> , 2013 , 34, 873-875	4.4	26
94	HfO ₂ -Based Highly Stable Radiation-Immune Ferroelectric Memory. <i>IEEE Electron Device Letters</i> , 2017 , 38, 330-333	4.4	25
93	Investigating the impact and reaction pathway of toluene on a SOFC running on syngas. <i>International Journal of Hydrogen Energy</i> , 2014 , 39, 12083-12091	6.7	25
92	Resistive switching mechanism of Ag/ZrO ₂ :Cu/Pt memory cell. <i>Applied Physics A: Materials Science and Processing</i> , 2011 , 102, 915-919	2.6	25
91	Influence of Operating Conditions on Carbon Deposition in SOFCs Fuelled by Tar-Containing Biosyngas. <i>Journal of the Electrochemical Society</i> , 2011 , 158, B1310	3.9	25

90	Memristive technologies for data storage, computation, encryption, and radio-frequency communication. <i>Science</i> , 2022 , 376,	33.3	24
89	Investigation of LRS dependence on the retention of HRS in CBRAM. <i>Nanoscale Research Letters</i> , 2015 , 10, 61	5	23
88	Investigation on the RESET switching mechanism of bipolar Cu/HfO ₂ /Pt RRAM devices with a statistical methodology. <i>Journal Physics D: Applied Physics</i> , 2013 , 46, 245107	3	23
87	. <i>IEEE Electron Device Letters</i> , 2010 ,	4.4	23
86	Improving the electrical performance of resistive switching memory using doping technology. <i>Science Bulletin</i> , 2012 , 57, 1235-1240		22
85	A Review for Compact Model of Thin-Film Transistors (TFTs). <i>Micromachines</i> , 2018 , 9,	3.3	22
84	Highly fluorescent hyperbranched BODIPY-based conjugated polymer dots for cellular imaging. <i>Chemical Communications</i> , 2017 , 53, 8612-8615	5.8	21
83	Advancements in organic nonvolatile memory devices. <i>Science Bulletin</i> , 2011 , 56, 3178		21
82	Degradation of Gate Voltage Controlled Multilevel Storage in One Transistor One Resistor Electrochemical Metallization Cell. <i>IEEE Electron Device Letters</i> , 2015 , 36, 555-557	4.4	20
81	. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1556-1558	4.4	20
80	Effects of interaction between defects on the uniformity of doping HfO ₂ -based RRAM: a first principle study. <i>Journal of Semiconductors</i> , 2013 , 34, 032001	2.3	20
79	Polaron effect and energetic disorder dependence of Seebeck coefficient in organic transistors. <i>Organic Electronics</i> , 2015 , 16, 113-117	3.5	18
78	Investigation on interface related charge trap and loss characteristics of high-k based trapping structures by electrostatic force microscopy. <i>Applied Physics Letters</i> , 2011 , 99, 223504	3.4	18
77	Effect of dipole layer on the density-of-states and charge transport in organic thin film transistors. <i>Applied Physics Letters</i> , 2013 , 103, 253303	3.4	17
76	Physical model of Seebeck coefficient under surface dipole effect in organic thin-film transistors. <i>Organic Electronics</i> , 2016 , 29, 27-32	3.5	16
75	A Dual-Functional IGZO-Based Device With Schottky Diode Rectifying and Resistance Switching Behaviors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 24-27	4.4	15
74	. <i>IEEE Electron Device Letters</i> , 2019 , 40, 718-721	4.4	14
73	Proton Radiation Effects on Y-Doped HfO ₂ -Based Ferroelectric Memory. <i>IEEE Electron Device Letters</i> , 2018 , 39, 823-826	4.4	14

72	Investigation on the Conductive Filament Growth Dynamics in Resistive Switching Memory via a Universal Monte Carlo Simulator. <i>Scientific Reports</i> , 2017 , 7, 11204	4.9	14
71	Reset Instability in $\text{Cu}/\text{HfO}_2/\text{Pt}$ RRAM Device. <i>IEEE Electron Device Letters</i> , 2011 , 32, 363-365	4.4	14
70	Fusion or non-fusion of quasi-two-dimensional fused perylene diimide acceptors: the importance of molecular geometry for fullerene-free organic solar cells. <i>Journal of Materials Chemistry A</i> , 2019 , 7, 27493-27502	13.3	14
69	A Compact Model for Drift and Diffusion Memristor Applied in Neuron Circuits Design. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 4290-4296	2.9	14
68	An overview of the switching parameter variation of RRAM. <i>Science Bulletin</i> , 2014 , 59, 5324-5337		13
67	Statistical characteristics of reset switching in Cu/HfO ₂ /Pt resistive switching memory. <i>Nanoscale Research Letters</i> , 2014 , 9, 2500	5	13
66	Response to "comment on real-time observation on dynamic growth/dissolution of conductive filaments in oxide-electrolyte-based ReRAM". <i>Advanced Materials</i> , 2013 , 25, 165-7	24	13
65	Differential conductance as a promising approach for rapid DNA sequencing with nanopore-embedded electrodes. <i>Applied Physics Letters</i> , 2010 , 97, 043701	3.4	13
64	Improved performance of non-volatile memory with Au-Al ₂ O ₃ core-shell nanocrystals embedded in HfO ₂ matrix. <i>Applied Physics Letters</i> , 2012 , 100, 203509	3.4	13
63	Hybrid memristor-CMOS neurons for in-situ learning in fully hardware memristive spiking neural networks. <i>Science Bulletin</i> , 2021 , 66, 1624-1624	10.6	13
62	Evolution of the conductive filament system in HfO ₂ -based memristors observed by direct atomic-scale imaging.. <i>Nature Communications</i> , 2021 , 12, 7232	17.4	13
61	Room Temperature-Processed a-IGZO Schottky Diode for Rectifying Circuit and Bipolar 1D1R Crossbar Applications. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4087-4091	2.9	12
60	Highly improved resistive switching performances of the self-doped Pt/HfO ₂ :Cu/Cu devices by atomic layer deposition. <i>Science China: Physics, Mechanics and Astronomy</i> , 2016 , 59, 1	3.6	12
59	A unified physical model of Seebeck coefficient in amorphous oxide semiconductor thin-film transistors. <i>Journal of Applied Physics</i> , 2014 , 116, 104502	2.5	12
58	Threshold Switching and Conductance Quantization in Al/HfO ₂ /Si(p) Structures. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 04CD06	1.4	12
57	Approaches for improving the performance of filament-type resistive switching memory. <i>Science Bulletin</i> , 2011 , 56, 461-464		12
56	A Physical Model for the Statistics of the Set Switching Time of Resistive RAM Measured With the Width-Adjusting Pulse Operation Method. <i>IEEE Electron Device Letters</i> , 2015 , 36, 1303-1306	4.4	11
55	Limitation of the concept of transport energy in disordered organic semiconductors. <i>Europhysics Letters</i> , 2014 , 106, 17005	1.6	11

54	Effect of low constant current stress treatment on the performance of the Cu/ZrO ₂ /Pt resistive switching device. <i>Semiconductor Science and Technology</i> , 2012 , 27, 105007	1.8	11
53	Improved current distribution in resistive memory on flexible substrate using nitrogen-rich TaN electrode. <i>Applied Physics Letters</i> , 2012 , 101, 243507	3.4	11
52	Negative differential resistance effect induced by metal ion implantation in SiO film for multilevel RRAM application. <i>Nanotechnology</i> , 2018 , 29, 054001	3.4	11
51	Suppression of Filament Overgrowth in Conductive Bridge Random Access Memory by TaO/TaO Bi-Layer Structure. <i>Nanoscale Research Letters</i> , 2019 , 14, 111	5	10
50	Manipulating Polymer Donors Toward a High-Performance Polymer Acceptor Based On a Fused Perylene diimide Building Block With a Built-In Twisting Configuration. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 29765-29772	9.5	10
49	Resistive switching characteristics of Ti/ZrO ₂ /Pt RRAM device. <i>Chinese Physics B</i> , 2014 , 23, 117305	1.2	10
48	Simulation study of conductive filament growth dynamics in oxide-electrolyte-based ReRAM. <i>Journal of Semiconductors</i> , 2014 , 35, 104007	2.3	10
47	Modulating 3D memristor synapse by analog spiking pulses for bioinspired neuromorphic computing. <i>Science China: Physics, Mechanics and Astronomy</i> , 2018 , 61, 1	3.6	9
46	Effect of TiC Nano inclusions on Thermoelectric and Mechanical Performance of Polycrystalline In ₄ Se _{2.65} . <i>Journal of the American Ceramic Society</i> , 2015 , 98, 3813-3817	3.8	9
45	Carrier-transport-path-induced switching parameter fluctuation in oxide-based resistive switching memory. <i>Materials Research Express</i> , 2015 , 2, 046304	1.7	9
44	Operation methods of resistive random access memory. <i>Science China Technological Sciences</i> , 2014 , 57, 2295-2304	3.5	9
43	Understanding the transport mechanism of organic-inorganic perovskite solar cells: The effect of exciton or free-charge on diffusion length. <i>Organic Electronics</i> , 2019 , 66, 163-168	3.5	9
42	Investigation of Retention Behavior of TiO _x /Al ₂ O ₃ Resistive Memory and Its Failure Mechanism Based on Meyer-Neldel Rule. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 957-962	2.9	8
41	Three-state resistive switching in HfO ₂ -based RRAM. <i>Solid-State Electronics</i> , 2014 , 98, 38-44	1.7	8
40	Analysis on the Filament Structure Evolution in Reset Transition of Cu/HfO ₂ /Pt RRAM Device. <i>Nanoscale Research Letters</i> , 2016 , 11, 269	5	8
39	Highly scalable resistive switching memory in metal nanowire crossbar arrays fabricated by electron beam lithography. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 02G105	1.3	8
38	High-Contrast Polymorphic Luminogen Formed through Effect of Tiny Differences in Intermolecular Interactions on the Intramolecular Charge Transfer Process. <i>Advanced Optical Materials</i> , 2020 , 8, 2000436	8.1	8
37	Low temperature atomic layer deposited HfO ₂ film for high performance charge trapping flash memory application. <i>Semiconductor Science and Technology</i> , 2014 , 29, 045019	1.8	7

36	Gate induced resistive switching in 1T1R structure with improved uniformity and better data retention 2014 ,		7
35	A Highlight of the Mechanisms of Immune Checkpoint Blocker Resistance. <i>Frontiers in Cell and Developmental Biology</i> , 2020 , 8, 580140	5.7	7
34	Simultaneous near-infrared and green fluorescence from single conjugated polymer dots with aggregation-induced emission fluorogen for cell imaging. <i>Journal of Materials Chemistry B</i> , 2018 , 6, 7871-7876	7.3	7
33	Design, Construction, and Testing of a Gasifier-Specific Solid Oxide Fuel Cell System. <i>Energies</i> , 2018 , 11, 1985	3.1	7
32	Performance-improved nonvolatile memory with aluminum nanocrystals embedded in Al ₂ O ₃ for high temperature applications. <i>Journal of Applied Physics</i> , 2011 , 110, 104514	2.5	6
31	Nonvolatile memory devices based on organic field-effect transistors. <i>Science Bulletin</i> , 2011 , 56, 1325-1332		6
30	Comparison of discrete-storage nonvolatile memories: advantage of hybrid method for fabrication of Au nanocrystal nonvolatile memory. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 035109	3	6
29	Fascin inhibitor increases intratumoral dendritic cell activation and anti-cancer immunity. <i>Cell Reports</i> , 2021 , 35, 108948	10.6	6
28	A cell-based clustering model for the reset statistics in RRAM. <i>Applied Physics Letters</i> , 2017 , 110, 123503	3.4	5
27	Origin of negative resistance in anion migration controlled resistive memory. <i>Applied Physics Letters</i> , 2018 , 112, 133108	3.4	5
26	FPAAs Based on Integration of CMOS and Nanoscale Devices for Neuromorphic Applications. <i>Lecture Notes of the Institute for Computer Sciences, Social-Informatics and Telecommunications Engineering</i> , 2009 , 44-48	0.2	5
25	Temperature, electric-field, and carrier-density dependence of hopping magnetoresistivity in disordered organic semiconductors. <i>Physical Review B</i> , 2017 , 96,	3.3	4
24	Optimization of Electrical Properties of MoS ₂ Field-Effect Transistors by Dipole Layer Coulombic Interaction With Trap States. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1900007	2.5	4
23	Observing large ferroelectric polarization in top-electrode-free Al:HfO ₂ thin films with Al-rich strip structures. <i>Applied Physics Letters</i> , 2019 , 115, 152901	3.4	3
22	Effect of bandgap engineering on the performance and reliability of a high-k-based nanoscale charge trap flash memory. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 065104	3	3
21	Nanoelectrodes: Enhanced DNA Sequencing Performance Through Edge-Hydrogenation of Graphene Electrodes (Adv. Funct. Mater. 14/2011). <i>Advanced Functional Materials</i> , 2011 , 21, 2602-2602	15.6	3
20	Resistive switching mechanism of Cu doped ZrO ₂ -based RRAM 2010 ,		3
19	From dielectric failure to memory function: Learning from oxide breakdown for improved understanding of resistive switching memories 2011 ,		3

18	CMOS Compatible Nonvolatile Memory Devices Based on SiO ₂ /Cu/SiO ₂ Multilayer Films. <i>Chinese Physics Letters</i> , 2011 , 28, 077201	1.8	3
17	Charge storage characteristics of metal-induced nanocrystalline in erbium-doped amorphous silicon films. <i>Thin Solid Films</i> , 2008 , 516, 7657-7660	2.2	3
16	Resistive switching memory for high density storage and computing*. <i>Chinese Physics B</i> , 2021 , 30, 058702.2		3
15	Engineering Non-fullerene Acceptors as a Mechanism to Control Film Morphology and Energy Loss in Organic Solar Cells. <i>Energy & Fuels</i> ,	4.1	3
14	Programme of self-reactive innate-like T cell-mediated cancer immunity.. <i>Nature</i> , 2022 ,	50.4	3
13	Carrier thermoelectric transport model for black phosphorus field-effect transistors. <i>Chemical Physics Letters</i> , 2017 , 678, 271-274	2.5	2
12	Transcriptomic profiling comparison of YAP over-expression and conditional knockout mouse tooth germs. <i>Genomics Data</i> , 2015 , 5, 228-30		2
11	Resistance-switching mechanism of SiO ₂ :Pt-based Mott memory. <i>Journal of Applied Physics</i> , 2015 , 118, 245701	2.5	2
10	Cell-based models for the switching statistics of RRAM 2011 ,		2
9	Modulating the filament rupture degree of threshold switching device for self-selective and low-current nonvolatile memory application. <i>Nanotechnology</i> , 2020 , 31, 144002	3.4	2
8	Improving the resistive switching reliability via controlling the resistance states of RRAM 2015 ,		1
7	Effect of Pulse and dc Formation on the Performance of One-Transistor and One-Resistor Resistance Random Access Memory Devices. <i>Chinese Physics Letters</i> , 2015 , 32, 028502	1.8	1
6	Programming resistive switching memory by a charged capacitor. <i>Applied Physics A: Materials Science and Processing</i> , 2011 , 102, 1003-1007	2.6	1
5	Formation and annihilation of Cu conductive filament in the nonpolar resistive switching Cu/ZrO ₂ :Cu/Pt ReRAM 2010 ,		1
4	Low-cost 13.56MHz Rectifier Based on Organic Diode. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1402, 13		1
3	Thermoelectric Seebeck Effect of Disordered Organic Semiconductors 2019 , 79-111		
2	High-Efficiency Energy Systems with Biomass Gasifiers and Solid Oxide Fuel Cells 2014 , 503-524		
1	Resistive Switching Devices: Mechanism, Performance and Integration 2019 , 843-911		

